

WHAT IS CLAIMED IS:

1. A semiconductor memory device comprising:
 - a semiconductor substrate;
 - a pair of field effect transistors associated with said semiconductor
 - 5 substrate wherein each source of said transistors shares a common impurity doped region formed in a plateau elevated from said semiconductor substrate and each gate electrode of said transistors is formed over each channel region of said transistors;
 - a first capacitor connected to a drain of one of said transistors;
 - a second capacitor connected to a drain of another one of said
 - 10 transistors.
- wherein said each of said first and second capacitors comprises a pair of electrodes and a dielectric layer interposed therebetween, said dielectric layer comprising a ferroelectric material, and
- wherein each of said first and second capacitors is located over said
- 15 gate electrode of the corresponding transistor so as to completely overlap said gate electrode.